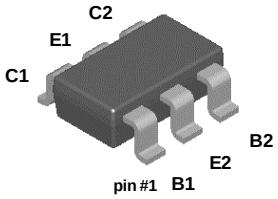
FAIRCHILD
SEMICONDUCTOR TM

FMB200



SuperSOT™-6
Mark: .N2
Dot denotes pin #1

PNP Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 68.

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FMB200	
P_D	Total Device Dissipation Derate above 25°C	700 5.6	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	°C/W

PNP Multi-Chip General Purpose Amplifier
(continued)

Electrical Characteristics
T_A = 25°C unless otherwise noted

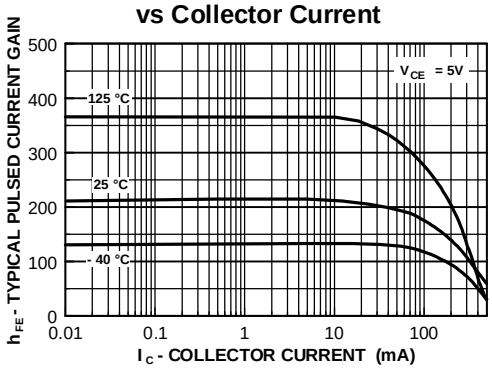
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 10 μA, I_B = 0	60			V
BV_{CEO}	Collector-Emitter Breakdown Voltage*	I_C = 1.0 mA, I_E = 0	45			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 10 μA, I_C = 0	6.0			V
I_{CBO}	Collector Cutoff Current	V_{CB} = 50 V, I_E = 0			50	nA
I_{CES}	Collector Cutoff Current	V_{CE} = 40 V, I_E = 10			50	nA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 4.0 V, I_C = 0			50	nA
ON CHARACTERISTICS						
h_{FE}	DC Current Gain	I_C = 100 μA, V_{CE} = 1.0 V I_C = 10 mA, V_{CE} = 1.0 V I_C = 150 mA, V_{CE} = 5.0 V*	80 100 100		 450 350	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 200 mA, I_B = 20 mA*			0.2 0.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 200 mA, I_B = 20 mA*			0.85 1.0	V V
SMALL SIGNAL CHARACTERISTICS						
f_T	Current Gain - Bandwidth Product	V_{CE} = 20 V, I_C = 20 mA		300		MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, f = 1.0 MHz		4.5		pF
NF	Noise Figure	I_C = 100 μA, V_{CE} = 5.0 V, R_G = 2.0 kΩ, f = 1.0 kHz		2.5		dB

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

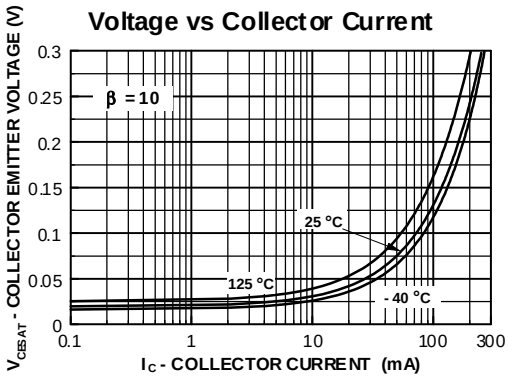
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current

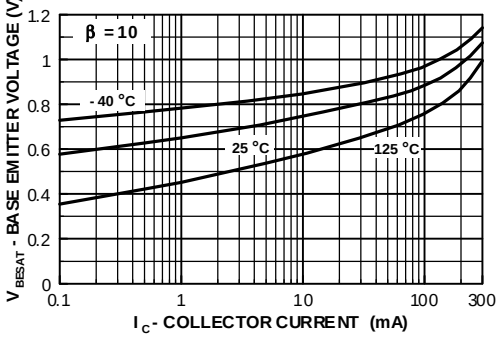


Collector-Emitter Saturation Voltage vs Collector Current

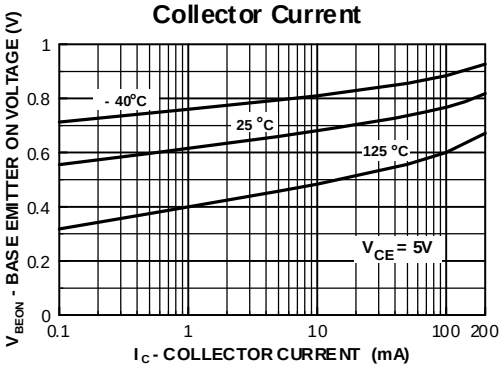


Typical Characteristics (continued)

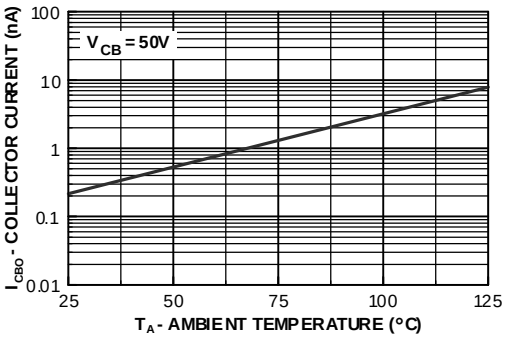
Base-Emitter Saturation Voltage vs Collector Current



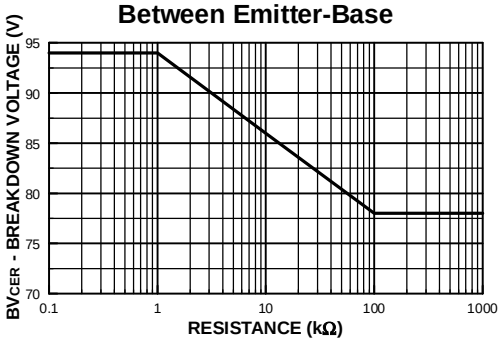
Base Emitter ON Voltage vs Collector Current



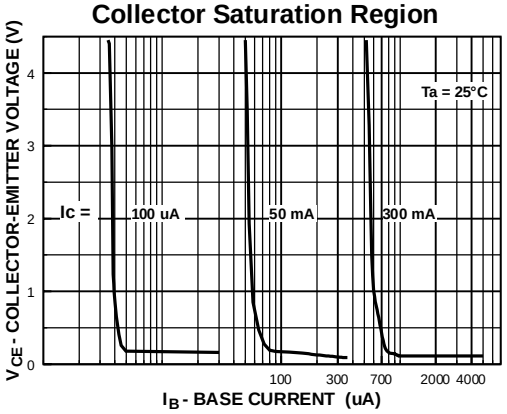
Collector-Cutoff Current vs Ambient Temperature



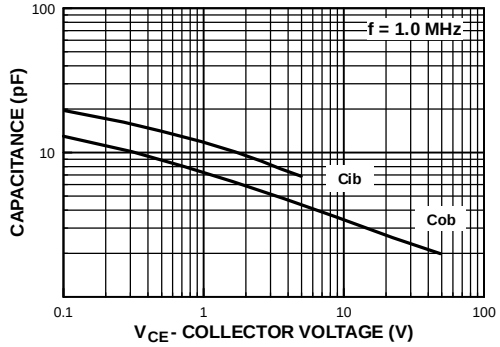
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Collector Saturation Region



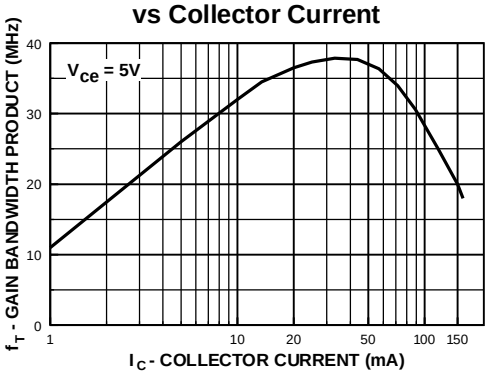
Input and Output Capacitance vs Reverse Voltage



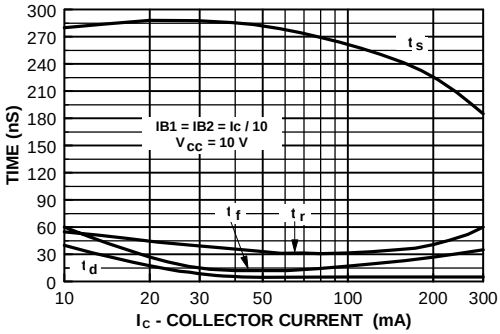
PNP Multi-Chip General Purpose Amplifier
(continued)

Typical Characteristics (continued)

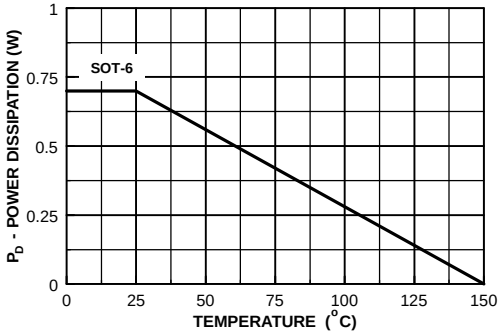
Gain Bandwidth Product vs Collector Current



Switching Times vs Collector Current



Power Dissipation vs Ambient Temperature



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